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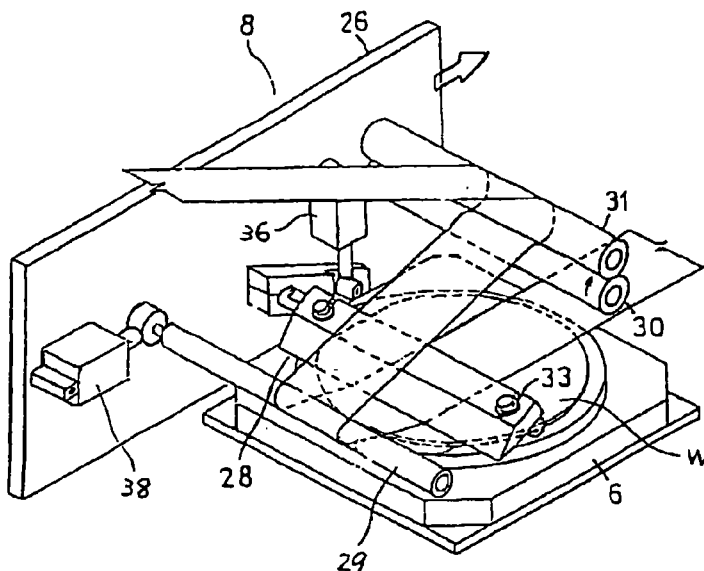
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(54) Title: METHOD AND APPARATUS FOR REMOVING UNWANTED SUBSTANCE FROM SEMICONDUCTOR WAFER



(57) Abstract: An apparatus for removing an unwanted substance from a semiconductor wafer, according to this invention, applies a peeling tape (T) to a protective tape (P) on the surface of the semiconductor wafer (W). An edge member (28) is placed in contact with the surface of the peeling tape (T) and run along the protective tape (P). The peeling tape (T) is peeled as being folded back by a large angle of 90 degrees or more at the tip of edge member (28). The protective tape (P) is peeled and removed along with the peeling tape (T) from the surface of the wafer. As a result, the unwanted substance is removed with high precision without breaking the wafer (W).

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